### **FORM PTO-1449**

## LIŞT OF PATENTS AND OTHER ITEMS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT

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**SERIAL NO.** 09/621/028

**APPLICANT:** 

Bergman, Eric J. et al.

FILING DATE: July 21, 2000 GROUP:

	HOA	0 1 2000	U.S. 8	PATENT DOCUMENTS			
EXAMINER INITIAL	TENTS	MENT NUMBER	DATE	NAME	CLASS	SUB CLASS_	FILING DATE
ZE	AA	5,055,138	10/8/91	Slinn	<del></del>		
	AB	5,120,370	6/9/92	Mori et al.			
	AC	5,647,386	7/15/97	Kaiser		*	
	AD	5,181,985	1/26/93	Lampert et al.			
	AE	5,503,708	4/2/96	Koizumi et al.			
	AF	5,464,480	11/7/95	Matthews			
	AH	5,308,745	5/3/94	Schwartzkopf			
	AI	4,695,327	9/22/87	Grebinski			
	AJ	5,632,847	5/27/97	Ohno et al.			
	AK	5,911,837	6/15/99	Matthews			
	AL	5,705,089	1/6/98	Sugihara et al.		- I'E	
	AM	5,244,000	9/14/93	Stanford et al.		CH	
	AN	5,714,203	2/3/98	Schellenberger et al.		ТЕСНИОСОС	
	AO	5,896,875	4/27/99	Yoneda			
	AP	4,974,530	12/4/90	Lyon		CENTER 1700	VEI
	AQ	5,055,138	10/8/91	Slinn	-	170	
	AR	5,120,370	6/9/92	Mori et al.		-	
	AS	5,647,386	7/15/97	Kaiser			
	AT	5,248,380	9/28/93	Tanaka			
	AU	5,520,744	5/28/96	Fujikawa et al.			· · · · · · · · · · · · · · · · · · ·
			5/16/95	Mashimo et al.			
ZE	AW	5,415,191			-		
	AW	5,658,615	8/19/97	Hasebe et al.			

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Information Disclosure Statement – Section 9 PTO-1449

#### FORM PTO-1449 ATTY. DOCKET **SERIAL NO.** 255/236 P00-0021 09/621/028 LIST OF PATENTS AND OTHER ITEMS FOR APPLICANT'S APPLICANT: INFORMATION DISCLOSURE STATEMENT Bergman, Eric J. et al. NOV 0 1 2000 **FILING DATE: GROUP:** (Use several sheets if necessary) July 21, 2000 THADENA 1/12/99 Chao et al. クド AX 5,858,107 5,235,995 8/17/93 Bergman et al. AY 1/3/95 ΑZ 5,378,317 Kashiwase et al. 5,971,368 10/26/99 Nelson et al. BA ZE 8/10/93 BB 5,234,540 Grant et al. FOREIGN PATENT DOCUMENTS TRANSLATION **EXAMINER** SUB YES NO INITIAL DOCUMENT NUMBER **COUNTRY CLASS** DATE CLASS BC 0 548 596 A2 6/3/93 Europe 12/6/89 BD 0 344 764 Europe BE 0 702 399 3/20/96 Europe BF GB 2 287 827 9/27/95 United Kingdom セセ BG JP52-12063 Japan OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.) Abstract of JP 3041729 published 2/22/91 BH 2F ΒI Abstract of JP 1008630, published 1/12/89 BJ Abstract of Japanese Appln. No. 63-16127 published July 31, 1989. BK Abstract of Japanese Appln. No. 52-100473 published March 14, 1979. Abstract of Japanese Appln. No. 1-192712 published March 12, 1992. BL Translation/Abstract of Japanese Appln. No. 1984-125760 published January 10, 1986. BM Heyns, M.M., et al. "New Wet Cleaning Strategies for Obtaining Highly Reliable Thin Oxides," MRP Symposium Proceedings on Materials Research Society, Spring Meeting, San Francisco, CA April 12-13, 1993, p. 35 (1993) BN Adler, Marilyn Grace and Hall, George Richard, "The Kinetics and Mechanism of Hydroxide Ion Catalyzed Ozone BO Decomposition in Aqueous Solution" J.Am. Chem. Soc., Volume 72, pp. 1884-86, 1950.

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Christenson, Kurt K., et al. "Deionized Water Helps Remove Wafer Stripping 'Resist'-ance." ZE www.precisioncleaningweb.com - Precision Cleaning Web - Archives, pp. 10-20 (April 1998) Sehested, K., et al., "Decomposition of Ozone in Aqueous Acid Solutions (pH 0-4)," J. Phys. Chem., pp. 1005-BR 1009 (1992) Krusell, W.C. et al., "Cleaning Technology for High Volume Production of Silicon Wafers," ECS Proc. of the BS First Int'l. Symposium on Cleaning Technology I Semiconductor Device Mfg.," pp. 23-32 (October 1989) BTVig, John R., "UV/Ozone Cleaning of Surfaces," U.S. Army Elec. Tech. and Devices Lab., pp. 1-26 Vig, John R., "UV/Ozone Cleaning of Surfaces: A Review," Surface Contamination: Genesis, Detection, and BU Control, pp. 235-253(1979) Tong, Jeremy, et al., "Aqueous Ozone Cleaning of Silicon Wafers," ECS Extended Abstracts, Phoenix, AZ, BW Abstract No. 506, pp. 753 (October 13-17, 1991) Zafonte, Leo, et al., "UV/Ozone Cleaning For Organics Removal on Silicon Wafers," SPIE Optical BXMicrolithography III: Technology for the Next Decade, Vol. 470, pp. 164-175 (1984) Baumgärtner, H., et al., "Ozone Cleaning of the SI-SIO<sub>2</sub> System," Appl. Phys. A, Vol. 43, pp. 223-226 (1987) BY Isagawa, Tatsuhiko, et al., "Ultra Clean Surface Preparation Using Ozonized Ultrapure Water," Extended Abstracts BZof the 1982 Int'l. Conf. on Solid State Devices and Materials, pp. 193-195 (1992) Shimada, H., et al., "Residual-Surfactant-Free Photoresist Development Process," J. Electrochem., Soc., CA 139(6):1721-1730 (June 1992) Tong, Jeremy K. et al., "Aqueous Ozone Cleaning of Silicon Wafers," Proc. of 2<sup>nd</sup> Int'l. Symposium on Cleaning Tech. In Semiconductor Device Mfg., pp. 18-25 (October 1992) CB CC Tong, Jeremy K., et al., "Aqueous Ozone Cleaning of Silicon Wafers," Res. Soc. Symp., pp. 18-25 (1993) Ohmi, T., et al., "Native Oxide Growth and Organic Impurity Removal on Si Surface with Ozone-Injected CD Ultrapure Water," J. Electrochem. Soc., 140(3):804-810 (March 1993) Vig. John R., et al., "UV/Ozone Cleaning of Surfaces," IEEE Transactions on Parts, Hybrids, and Packaging, Vol. CE PHP-12(4):365-370 (December 1976) Vig, John R., "UV/ozone cleaning of surfaces," U.S. Army Electronics Technology and Devices Laboratory **CF** ERADCOM, Ft. Monmouth, NJ, 07703-5302, pp. 1027-1034 (September/October 1984) Tabe, Michiharu, "UV ozone cleaning of silicon substrates in silicon molecular beam epitaxy," Appl. Phys. Lett., CG 45(10):1073-1075 (November 1984) Zazzera, L.A., et al., "XPS and SIMS Study of Anhydrous HF and UV/Ozone-Modified Silicon (100) Surfaces," J. CH Electrochem. Soc., 136(2):484-491 (February 1989) Gabriel, Calvin, et al., "Reduced Device Damage Using An Ozone Based Photoresist Removal Process," SPIE CI Advances in Resist Technology and Processing VI, Vol. 1086, pp. 598-604 (1989) Suemitsu, Maki, et al., "Low Temperature Silicon Surface Cleaning by HF Etching/Ultraviolet Ozone Cleaning (HF/UVOC) Method (I) -Optimization of the HF Treatment-," Japanese Journal of Applied Physics, 28(12):2421-CJ 2424 (December 1989) Kern, Werner, "The Evolution of Silicon Wafer Cleaning Technology," J. Electrochem. Soc., 137(6):1887-1892 CK (June 1990) Kasi, S.R., et al., "Surface Hydrocarbon Removal from Si by UV/Ozone," ECS Extended Abstracts, No. 458, pp. CL Kasi, Srinandan R., et al., "Vapor phase hydrocarbon removal for Si processing," Appl. Phys. Lett., 57(20):2095-2 CM 2097 (November 1990)

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**SERIAL NO.** 09/621/028

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Bergman, Eric J. et al.

FILING DATE: July 21, 2000 **GROUP:** 

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